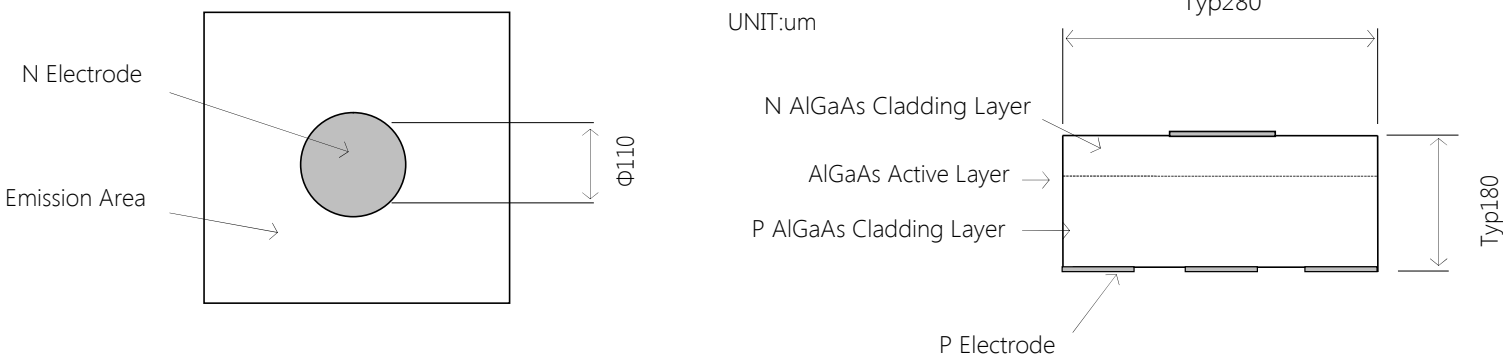


| Radiation | Type | Electrodes |
|-----------|--------|----------------|
| Infrared | AlGaAs | N (cathode) up |



Physical Characteristics & Structure

| | |
|------------------------------|----------------------------------|
| Material: AlGaAs | Bond Pad Size: 110um diameter |
| Junction Size: 280um x 280um | Anode Metalization: Gold Alloy |
| Thickness: 180um | Cathode Metalization: Gold Alloy |

Electrical & Optical Characteristics (Ta = 25°C)

| ITEMS | SYMBOL | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------|--------|------------|-----|-----|-----|------|
| Forward Voltage | Vf | If=20mA | -- | -- | 1.6 | V |
| Reverse Voltage | Vr | Ir=10uA | 5 | -- | -- | V |
| Radiant Power* | Φe | If=20mA | 4.0 | -- | -- | mW |
| Peak Wavelength | λp | If=20mA | -- | 850 | -- | nm |
| Spectral Bandwidth at 50% | Δλ0.5 | If=20mA | -- | 40 | -- | nm |

* LED chip is mounted on TO-18 gold header without resin coated.

Absolute Maximum Ratings (Ta = 25°C)

Continuous Maximum Forward Current: 80mA (DC)
 Reverse Voltage: 5V (IR=10uA)
 Storage Temperature
 while on mylar membrane: 0 to 40 °C
 after removal from mylar membrane: -30 to 100 °C



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.